

IGBT Module

PSIG 160/12

PSIS 160/12*

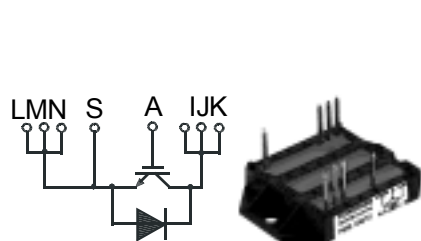
PSSI 160/12*

$$\begin{aligned} I_{C25} &= 169 \text{ A} \\ V_{CES} &= 1200 \text{ V} \\ V_{CE(sat)typ.} &= 2.9 \text{ V} \end{aligned}$$

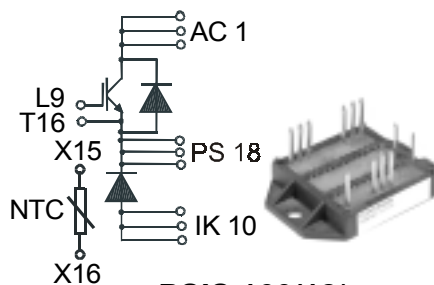
Short Circuit SOA Capability

Square RBSOA

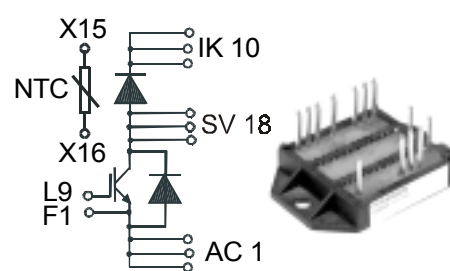
Preliminary Data Sheet



PSIG 160/12



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IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	169	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	117	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 6.8 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA, Clamped inductive load; $L = 100 \mu\text{H}$	200 V_{CES}	A
t_{SC} (SCSOA)	$V_{CE} = V_{CES}; V_{GE} = \pm 15 \text{ V}; R_G = 6.8 \Omega; T_{VJ} = 125^{\circ}\text{C}$ non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	694	W

*NTC optional

Features

- Package with DCB ceramic base plate
- Isolation voltage 3000 V~
- Planar glass passivated chips
- Low forward voltage drop
- Leads suitable for PC board soldering
- UL registered, E 148688

Applications

- AC and DC motor control
- AC servo and robot drives
- power supplies
- welding inverters

Advantages

- Easy to mount with two screws
- Space and weight savings
- Improved temperature and power cycling capability
- High power density
- Small and light weight
- Leads with expansion bend for stress relief

Caution: These Devices are sensitive to electrostatic discharge. Users should observe proper ESD handling precautions.

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)		
		min.	typ.	max.
$V_{CE(sat)}$	$I_C = 160 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		2.9 3.3	3.5 V
$V_{GE(th)}$	$I_C = 4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$			6 mA 19 mA
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			400 nA
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 100 \text{ A}$ $V_{GE} = 15/0 \text{ V}; R_G = 6.8 \Omega$		100 60 600 90 16.1 14.6	ns ns ns ns mJ mJ
C_{ies}			6.5	nF
R_{thJC} R_{thJH}	(per IGBT) with heatsink compound (0.42 K/m.K; 50 μm)		0.36	0.18 K/W K/W

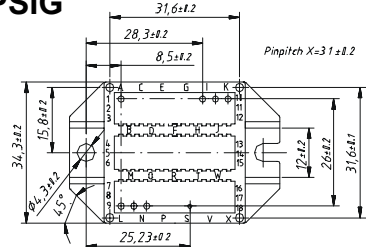
Reverse diodes (FRED)

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	154	A
I_{F80}	$T_C = 80^\circ\text{C}$	97	A

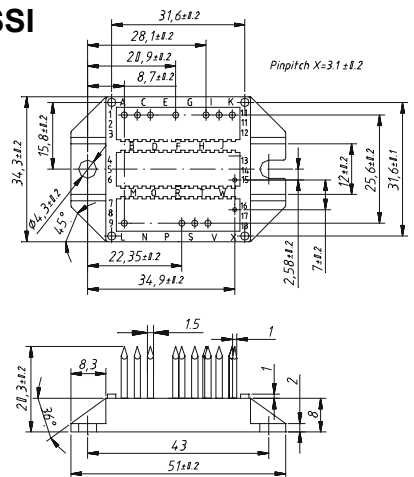
Package style and outline
Dimensions in mm (1mm = 0.0394")

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 100\text{ A}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.3	1.7	2.7 V
I_{RM} t_{tr}	$I_F = 75\text{ A}; di_F/dt = 750\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	79		A
		220		ns
R_{thJC} R_{thJH}	with heatsink compound (0.42 K/m.K; 50 μm)	0.9		0.45 K/W K/W

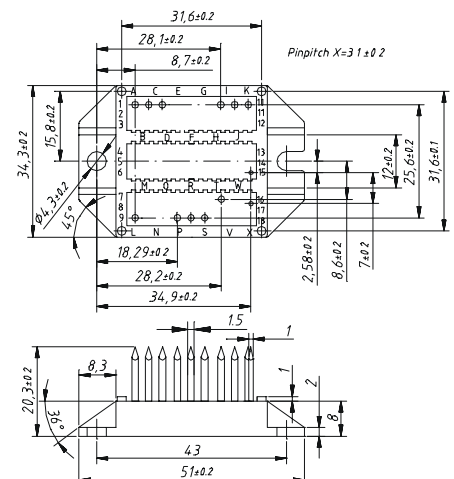
PSIG



PSSI



PSIS



Temperature Sensor NTC

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
R_{25}	$T = 25^\circ\text{C}$	4.75	5.0	5.25 k Ω
$B_{25/50}$			3375	K

Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}		-40...+150	$^\circ\text{C}$
T_{stg}		-40...+150	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	3000	V~
M_d	Mounting torque (M4)	1.5 - 2.0	Nm
		14 - 18	lb.in.
a	Max. allowable acceleration	50	m/s ²

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
d_s	Creepage distance on surface (Pin to heatsink)	11.2		mm
d_A	Strike distance in air (Pin to heatsink)	11.2		mm
Weight		24		g

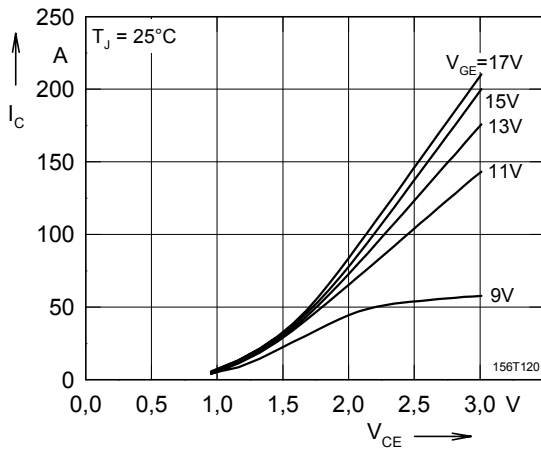


Fig. 1 Typ. output characteristics

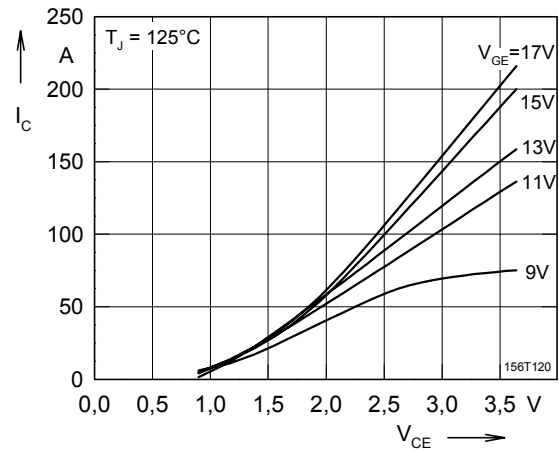


Fig. 2 Typ. output characteristics

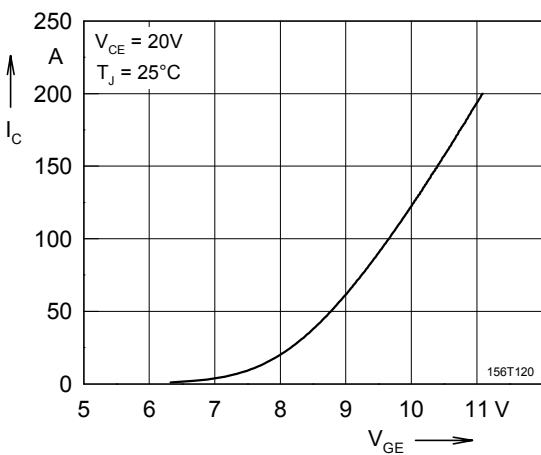


Fig. 3 Typ. transfer characteristics

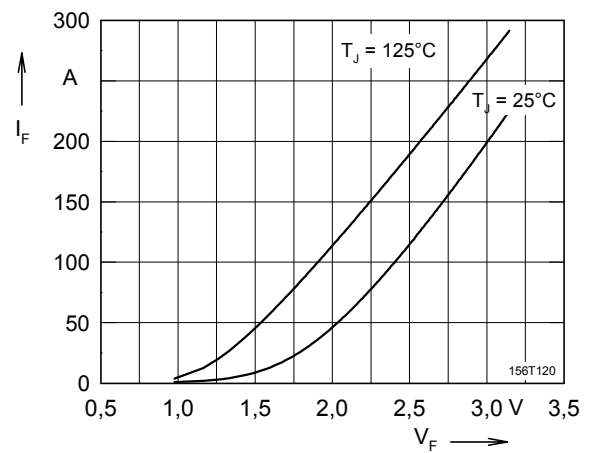


Fig. 4 Typ. forward characteristics of free wheeling diode

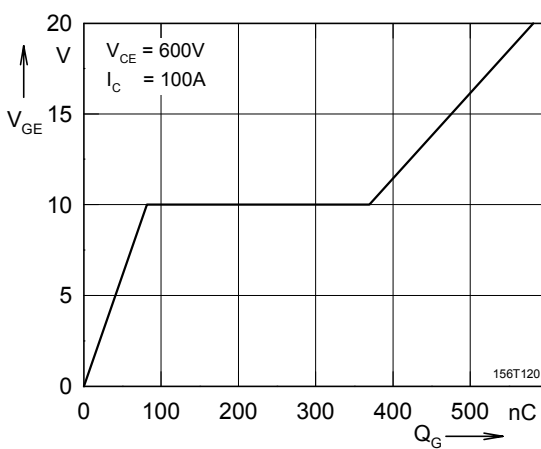


Fig. 5 Typ. turn on gate charge

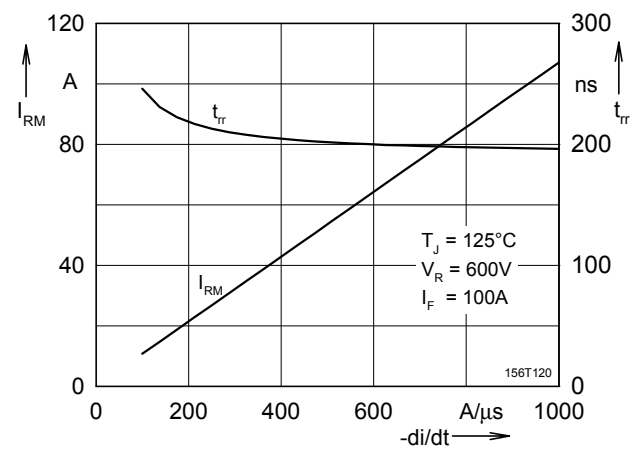


Fig. 6 Typ. turn off characteristics of free wheeling diode

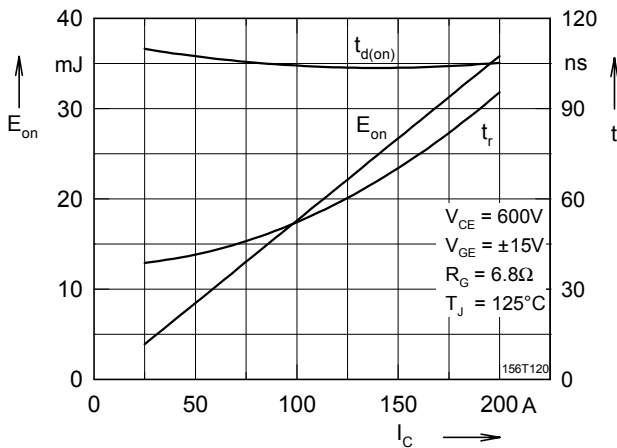


Fig. 7 Typ. turn on energy and switching times versus collector current

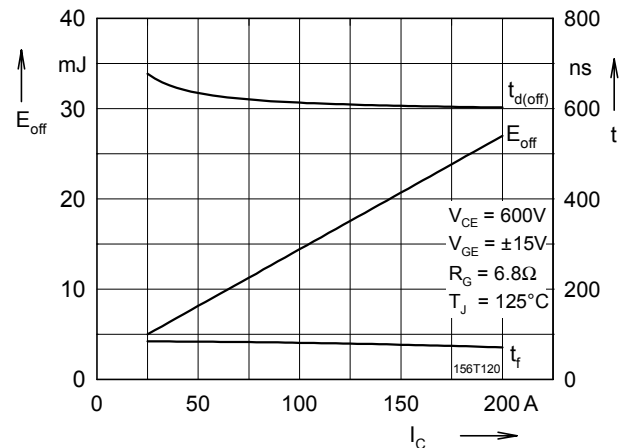


Fig. 8 Typ. turn off energy and switching times versus collector current

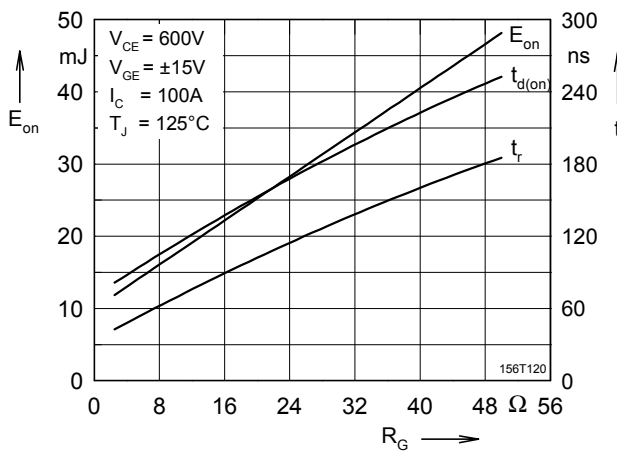


Fig. 9 Typ. turn on energy and switching times versus gate resistor

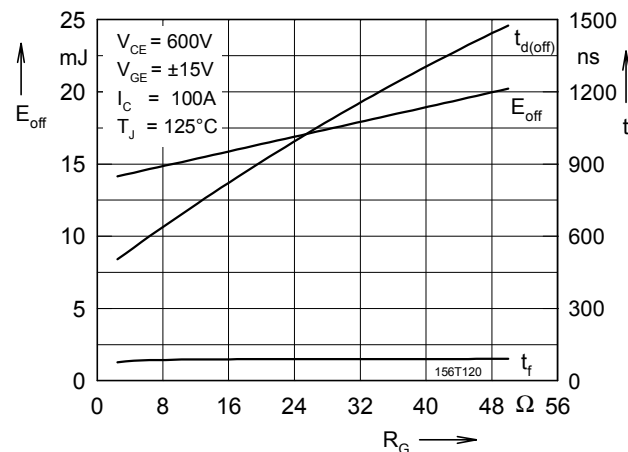


Fig. 10 Typ. turn off energy and switching times versus gate resistor

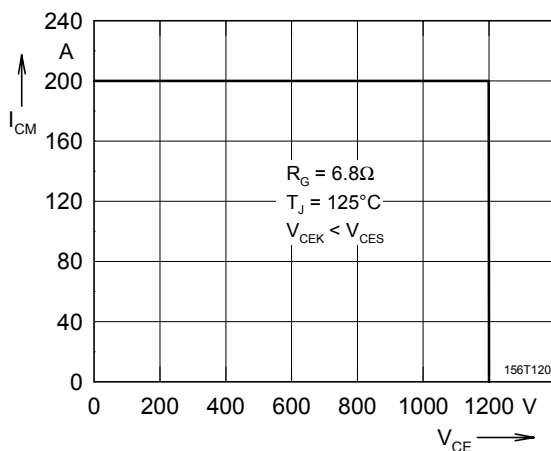


Fig. 11 Reverse biased safe operating area RBSOA

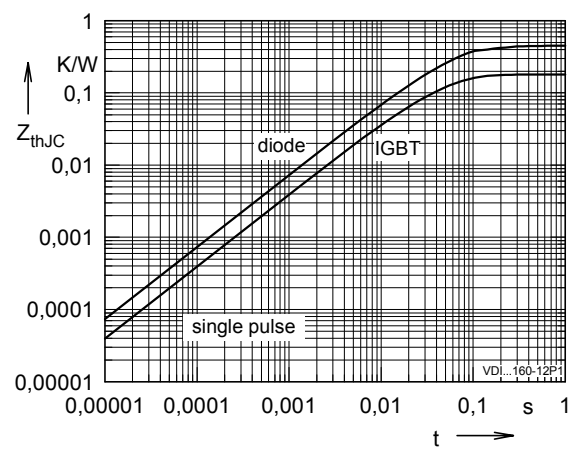


Fig. 12 Typ. transient thermal impedance